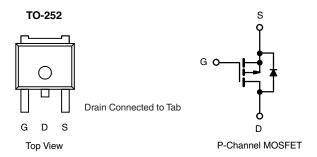


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Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0155			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0200			
I _D (A)	- 50			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P06-15L-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 60		
Gate-Source Voltage		V_{GS}	± 20	- V	
Continuous Drain Currenta	T _C = 25 °C	1	- 50		
Continuous Drain Current	T _C = 125 °C	D ID	- 38		
Continuous Source Current (Diode Conduction)a	I _S	- 50	Α		
Pulsed Drain Current ^b	I _{DM}	- 200			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 52		
Single Pulse Avalanche Energy		E _{AS}	135	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C P _D		136	W	
Maximum Fower Dissipation	T _C = 125 °C	r D	45	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.1		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	-	-					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-	- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = - 60 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 125 °C	-	-	- 50	μΑ
		V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≥ - 5 V	- 50	-	-	Α
		V _{GS} = - 10 V	I _D = - 17 A	-	0.0135	0.0155	Ω
Drain Cauras On State Resistance		V _{GS} = - 10 V	I _D = - 50 A, T _J = 125 °C	-	-	0.026	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 50 A, T _J = 175 °C	-	-	0.032	
		V _{GS} = - 4.5 V	I _D = - 14 A	-	0.017	0.020	
Forward Transconductancea	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		-	50		S
Dynamic ^b	<u> </u>	<u> </u>					
Input Capacitance	C _{iss}			-	4730	5910	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 25 V, f = 1 MHz	-	485	606	
Reverse Transfer Capacitance	C _{rss}	7		-	330	410	
Total Gate Charge ^c	Qg			-	98	150	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -30 \text{ V}, I_{D} = -50 \text{ A}$	-	15	23	nC
Gate-Drain Charge ^c	Q _{gd}	7		-	21	32	
Gate Resistance	R _g	f = 1 MHz		1.47	2.9	4.42	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	18	
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_L = 0.6 \Omega$ $I_D \cong -50 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 6.0 \Omega$		-	12	16	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	112	125	
Fall Time ^c	t _f			-	39	48	
Source-Drain Diode Ratings and Char	acteristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	- 200	Α
Forward Voltage	V _{SD}	I _F =	I _F = - 50 A, V _{GS} = 0 V		- 0.8	- 1.5	V

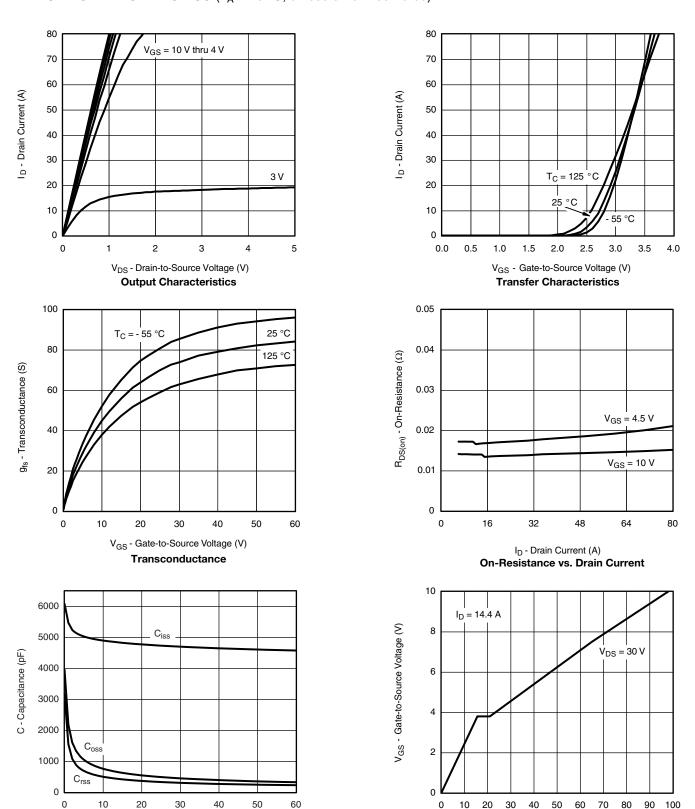
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Q_q - Total Gate Charge (nC)

Gate Charge

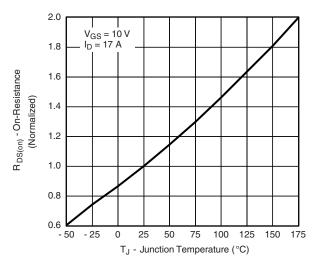
V_{DS} - Drain-to-Source Voltage (V)

Capacitance

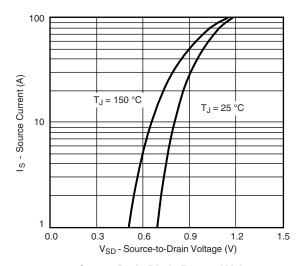


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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

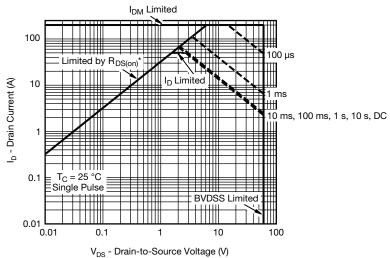


On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage

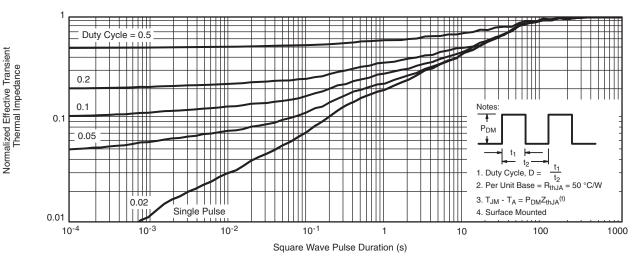
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



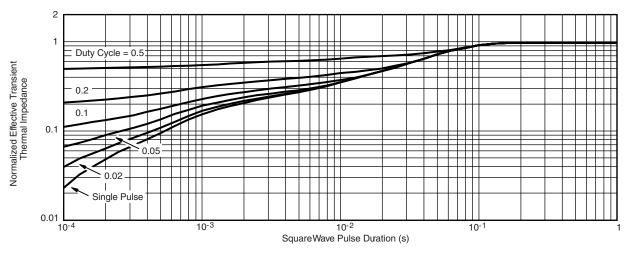
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25°C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69098.





TO-252AA Case Outline





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

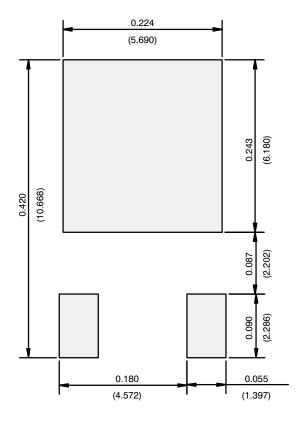
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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